

Low-power radio design for the IoT

Exercise 4 (24.03.2022)

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Problem 1 Low-power Common Source RF Design

The circuit in the Figure below is a single MOSFET Common Source (CS) Amplifier.

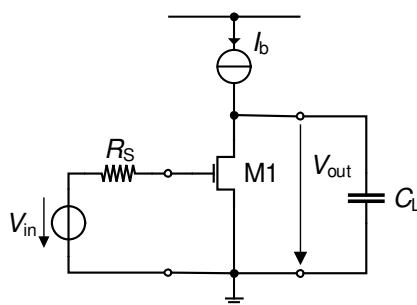


Figure 1: Common Source Amplifier.

- Find the optimum inversion coefficient of the common-source amplifier shown in ?? for maximizing the following figure-of-merit

$$FoM \triangleq \frac{\omega_u}{(F-1) \cdot I_b}. \quad (1)$$

- Calculate the bias current required to achieve a gain-bandwidth $f_u = 10 \text{ GHz}$ for a load capacitance $C_L = 10 \text{ fF}$ with $\lambda_c = 0.25$.
- Calculate the resulting noise factor F for a source impedance $R_S = 50 \Omega$.
- How can you reduce this noise factor?

Problem 2 Common Source Design

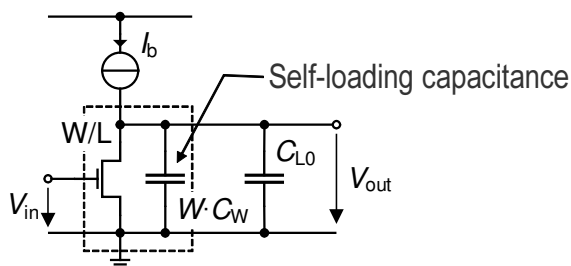


Figure 2: Common source amplifier including the self-loading capacitance.

The normalized bias current and aspect ratio for the CS amplifier

$$\begin{aligned} i_b &\triangleq \frac{I_D}{I_{spec\Box}} \cdot \frac{1}{\Omega} = \frac{IC}{g_{ms} - \Theta}; \\ AR &\triangleq \frac{W}{L} \cdot \frac{1}{\Omega} = \frac{1}{g_{ms} - \Theta}, \end{aligned} \quad (2)$$

where $\Omega \triangleq \frac{\omega_u}{\omega_L}$ and Θ is equal to $\frac{C_w L}{C_{L0}} \cdot \frac{\omega_u}{\omega_L} = \frac{\omega_u}{\omega_{t\text{spec}}}$.

Design the CS amplifier, shown in Fig. 2, for the following specifications at room temperature:

$$f_u = 18 \text{ MHz} \quad C_{L0} = 60 \text{ fF} \quad V_{DD} = 1.8 \text{ V} \quad L = 40 \text{ nm} \quad C_w = 0.450 \text{ fF/nm}, \quad (3)$$

and by assuming the following values for the technology parameters

$$I_{\text{spec}\square} = 950 \text{ nA} \quad n = 1.5 \quad V_{T0} = 455 \text{ mV} \quad \lambda_c = 0.4875 \quad L_{\text{sat}} = 19.5 \text{ nm}. \quad (4)$$

- Find the IC_{opt} , the value of the inversion coefficient for which the bias current is minimum. Assume no velocity saturation.
- Based on the IC_{opt} , find the values of the bias current, I_q , and the transistor aspect ratio, W/L , to achieve the specified gain-bandwidth, ω_u .